

SPECIFICATION AMENDMENTS

Please replace paragraph [0034] of the present specification with the following paragraph, which includes markings to show the changes made:

[0034] Numerous electronic devices can be formed according to the present invention including resistors, capacitors, diodes, memory devices, and electro-optical devices. For example, one particular type of electronic device includes three-dimensional memory devices as disclosed in co-pending US Patent Application Serial No. 09/560,626 titled "Three-Dimensional Memory Array and Method of Fabrication," filed April 28, 2000, which describes a three dimensional memory array including memory cells formed at numerous levels above a substrate, which is hereby fully incorporated by reference. Another example includes nonvolatile memory devices as disclosed in US Patent No. 6,034,882 titled "Vertically Stacked Field Programmable Nonvolatile Memory and Method of Fabrication," issued on March 7, 2000, which is hereby fully incorporated by reference. Still other examples include HBTs (heterojunction bipolar transistors) and TFTs (thin-film transistors), which can be formed by alternating layers of crystalline silicon (Si) with different doping types.